

XTR106 4mA ~ 20mA 電流トランスミッター、センサ励起および線形化機能付き

1 特長

- 低い全体未調整誤差
- 2.5V、5V のブリッジ励起リファレンス
- 5.1V レギュレータ出力
- 低いスパンドリフト: 最大値 $\pm 25\text{ppm}/^\circ\text{C}$
- 小さいオフセットドリフト: $0.25\mu\text{V}/^\circ\text{C}$
- 高い PSR: 110dB 以上
- 高い CMR: 86dB 以上
- 幅広い電源電圧範囲: 7.5V ~ 36V
- 14 ピン DIP および SOIC パッケージ オプション

2 アプリケーション

- フィールドトランスミッタとセンサ
- ファクトリオートメーション
- HART モデムと互換
- 圧力 / 温度ブリッジトランスミッター
- 産業用プロセス制御
- SCADA リモート データ アクイジション
- 計量システム
- ひずみゲージトランスミッタ
- 加速度計

3 概要

XTR106 は、コストを最適化したブリッジ センサ アプリケーション用に設計されたモノリシック 4mA ~ 20mA への 2 線式電流トランスミッターです。このデバイスは包括的なブリッジ励起 (2.5V または 5V の基準電圧)、計測アンプ、センサの線形化、電流出力回路を提供します。追加の外部入力回路に電力を供給するための電流は、 V_{REG} ピンから供給できます。

計装アンプは広いゲインで使用でき、さまざまな種類の入力信号に対応します。線形化ブリッジを含める電流トランスミッター全体の総合未調整誤差は十分に低く、多くのアプリケーションで調整なしに使用できます。XTR106 は、最低 7.5V のループ電源電圧で動作します。

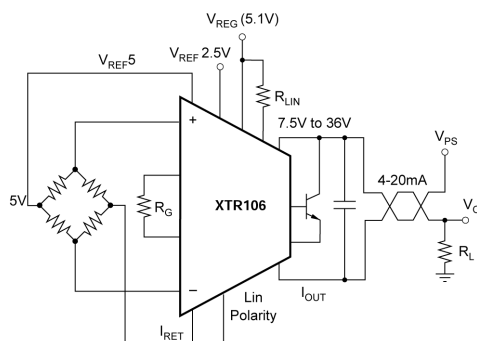
線形化回路は、ブリッジ励起電圧を制御することにより、伝達関数に 2 次補正を行います。このデバイスは、コスト最適化されたトランスデューサでも、非直線性が最大 20:1 改善されています。

XTR106 は 14 ピンのプラスチック DIP および SOIC 表面実装パッケージで供給され、 -40°C ~ $+85^\circ\text{C}$ の温度範囲で動作が規定されています。このデバイスは、 -40°C から $+125^\circ\text{C}$ の温度で動作します。

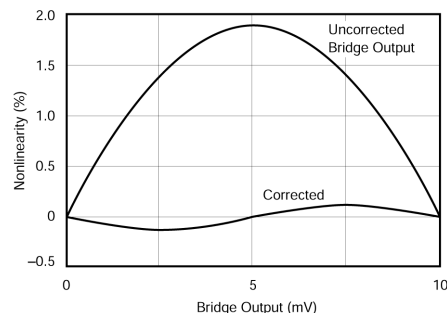
パッケージ情報

部品番号	パッケージ (1)	パッケージ サイズ (2)
XTR106	D (SOIC, 14)	8.65mm × 6mm
	N (PDIP, 14)	19.3mm × 9.4mm

- (1) 供給されているすべてのパッケージについては、[セクション 10](#) を参照してください。
- (2) パッケージ サイズ (長さ × 幅) は公称値であり、該当する場合はピンも含まれます。



XTR106 を使用したブリッジの非直線性補正 回路図



XTR106 ブリッジの非直線性補正



Table of Contents

1 特長	1	7.1 Application Information.....	17
2 アプリケーション	1	7.2 Typical Applications.....	23
3 概要	1	7.3 Layout.....	25
4 Pin Configuration and Functions	3	7.4 Layout Guidelines.....	25
5 Specifications	4	8 Device and Documentation Support	26
5.1 Absolute Maximum Ratings.....	4	8.1 Documentation Support.....	26
5.2 Recommended Operating Conditions.....	4	8.2 Related Documentation.....	26
5.3 Thermal Information.....	4	8.3 ドキュメントの更新通知を受け取る方法.....	26
5.4 Electrical Characteristics.....	5	8.4 サポート・リソース.....	26
5.5 Typical Characteristics.....	7	8.5 Trademarks.....	26
6 Detailed Description	11	8.6 静電気放電に関する注意事項.....	26
6.1 Overview.....	11	8.7 用語集.....	26
6.2 Functional Block Diagram.....	12	9 Revision History	26
6.3 Feature Description.....	12	10 Mechanical, Packaging, and Orderable	
6.4 Device Functional Modes.....	16	Information	27
7 Application and Implementation	17		

4 Pin Configuration and Functions

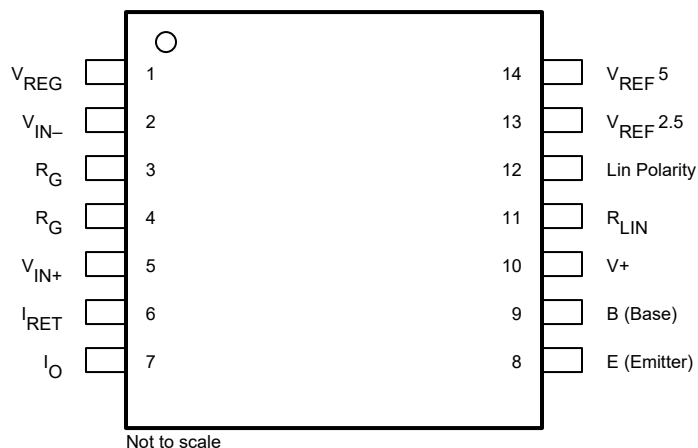


図 4-1. D Package, 14-Pin SOIC, and N Package, 14-Pin PDIP (Top View)

表 4-1. Pin Functions

PIN		TYPE	DESCRIPTION
NAME	NO.		
B (Base)	9	Output	Base connection for external transistor
E (Emitter)	8	Input	Emitter connection for external transistor
I _O	7	Output	Regulated 4mA to 20mA current loop output
I _{RET}	6	Input	Local ground return pin for V _{REG} , V _{REF5} , and V _{REF2.5}
Lin Polarity	12	Input	Linearity correction circuit polarity setting. Connect to I _{RET} to correct for positive nonlinearity, or connect to V _{REG} to correct for negative nonlinearity or if not using the linearity correction feature
R _G	3, 4	—	Input stage gain setting pins. The resistance R _G between pins 3 and 4 sets the gain of the voltage-to-current transfer function
R _{LIN}	11	—	Linearity correction resistor pin. The resistance R _{LIN} between pins 1 and 11 sets the corrective factor of the linearity correction circuit
V+	10	Power	Loop power supply
V _{IN-}	2	Input	Negative (inverting) differential voltage input
V _{IN+}	5	Input	Positive (noninverting) differential voltage input
V _{REF5}	14	Output	5V reference voltage output
V _{REF2.5}	13	Output	2.5V reference voltage output
V _{REG}	1	Output	5.1V regulator voltage output

5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V+	Power supply (referenced to IO pin)		40	V
	Input voltage, V_{IN+} or V_{IN-} (referenced to IRET pin)	0	V+	V
	Output current limit		Continuous	
T_A	Operating temperature	–40	125	°C
T_J	Junction temperature		165	°C
T_{stg}	Storage temperature	–55	125	°C
	Lead temperature (soldering, 10s)		300	°C

- (1) Operation outside the *Absolute Maximum Ratings* may cause permanent device damage. *Absolute Maximum Ratings* do not imply functional operation of the device at these or any other conditions beyond those listed under *Recommended Operating Conditions*. If used outside the *Recommended Operating Conditions* but within the *Absolute Maximum Ratings*, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime

5.2 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V+	Power supply (referenced to the I_O pin)	7.5	24	36	V
T_A	Specified temperature	–40		85	°C

5.3 Thermal Information

THERMAL METRICS ⁽¹⁾		XTR106		UNIT
		D (SOIC)	N (PDIP)	
		14 PINS		
R _{θJA}	Junction-to-ambient thermal resistance	86.8	51.8	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	46.9	29.4	°C/W
R _{θJB}	Junction-to-board thermal resistance	46.0	24.2	°C/W
Ψ _{JT}	Junction-to-top characterization parameter	9.6	7.8	°C/W
Ψ _{JB}	Junction-to-board characterization parameter	45.6	23.7	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC package thermal metrics](#) application note.

5.4 Electrical Characteristics

at $T_A = +25^\circ\text{C}$, $V_+ = 24\text{V}$, and TIP29C external transistor (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNITS
OUTPUT							
I _O	Output current equation			I _O = V _{IN} • (40/R _G) + 4mA, V _{in} in Volts, R _G in Ω			A
	Output current, specified range			4		20	mA
I _{OVER}	Overscale limit			24	28	30	mA
I _{UNDER}	Underscale limit	I _{REG} = 0, I _{REF} = 0		1	1.6	2.2	mA
		I _{REF} + I _{REG} = 2.5mA		2.9	3.4	4	
ZERO OUTPUT ⁽¹⁾ (V _{IN} = 0V, R _G = ∞)							
I _{ZERO}	Zero output				4		mA
	Initial error	XTR106P, XTR106U			±5	±25	μA
		XTR106PA, XTR106UA			±5	±50	
	vs temperature	T _A = −40°C to +85°C			±0.07	±0.9	μA/°C
	vs supply voltage, V+	V+ = 7.5V to 36V			0.04	0.2	μA/V
	vs common-mode voltage (CMRR)	V _{CM} = 1.1V to 3.5V ⁽⁵⁾			0.02		μA/V
	vs V _{REG} (I _O)				0.8		μA/mA
i _n	Noise: 0.1Hz to 10Hz				0.035		μAp-p
SPAN							
S	Span equation (transconductance)			S = 40/R _G			A/V
	Untrimmed error	Full scale (V _{IN}) = 50mV	XTR106P, XTR106U		±0.05	±0.2	%
			XTR106PA, XTR106UA		±0.05	±0.4	
	vs temperature ⁽²⁾	T _A = −40°C to +85°C			±3	±25	ppm/°C
	Nonlinearity: ideal input ⁽³⁾	Full scale (V _{IN}) = 50mV			±0.001	±0.01	%
INPUT ⁽⁴⁾							
V _{OS}	Offset voltage	V _{CM} = 2.5V	XTR106P, XTR106U		±50	±100	μV
			XTR106PA, XTR106UA		±50	±250	
	vs temperature	T _A = −40°C to +85°C	XTR106P, XTR106U		±0.25	±1.5	μV/°C
			XTR106PA, XTR106UA		±0.25	±3	
	vs supply voltage, V+	V+ = 7.5V to 36V			±0.1	±3	μV/V
CMRR	vs common-mode voltage, RTI	V _{CM} = 1.1V to 3.5V ⁽⁵⁾	XTR106P, XTR106U		±10	±50	μV/V
			XTR106PA, XTR106UA		±10	±100	
V _{CM}	Common-mode range ⁽⁵⁾			1.1		3.5	V
I _B	Input bias current	XTR106P, XTR106U			5	25	nA
		XTR106PA, XTR106UA			5	50	
	vs temperature	T _A = −40°C to +85°C			20		pA/°C
I _{OS}	Input offset current	XTR106P, XTR106U			±0.2	±3	nA
		XTR106PA, XTR106UA			±0.2	±10	
	vs temperature	T _A = −40°C to +85°C			5		pA/°C
Z _{IN}	Impedance: differential				0.1 1		GΩ pF
	Common-mode				5 10		GΩ pF
V _n	Noise: 0.1Hz to 10Hz				0.6		μVp-p

5.4 Electrical Characteristics (続き)

at $T_A = +25^\circ\text{C}$, $V_+ = 24\text{V}$, and TIP29C external transistor (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNITS
VOLTAGE REFERENCES ⁽⁵⁾ (Lin Polarity Connected to V _{REG} , R _{LIN} = 0)							
V _{REF} 2.5	Initial: 2.5V reference			2.5			V
V _{REF} 5	5V reference			5			V
	Accuracy	V _{REF} = 2.5V or 5V	XTR106P, XTR106U	±0.05	±0.25		%
			XTR106PA, XTR106UA	±0.05	±0.5		
	vs temperature ⁽⁶⁾	T _A = -40°C to +85°C	XTR106P, XTR106U	±20	±35		ppm/°C
			XTR106PA, XTR106UA	±20	±75		
	vs supply voltage, V+	V+ = 7.5V to 36V		±5	±20		ppm/V
	vs load	I _{REF} = 0mA to 2.5mA		60			ppm/mA
	Noise: 0.1Hz to 10Hz			10			μVp-p
V _{REG} ⁽⁵⁾							
	V _{REG}			5.1			V
	Accuracy			±0.02	±0.1		V
	vs temperature	T _A = -40°C to +85°C		±0.5			mV/°C
	vs supply voltage, V+	V+ = 7.5V to 36V		1			mV/V
I _{REG}	Output current			See Typical Curves			mA
	Output impedance	I _{REG} = 0mA to 2.5mA		80			Ω
LINEARIZATION ⁽⁷⁾							
R _{LIN}	R _{LIN} (external) equation			RLIN = KLIN • (4B/(1-2B)), K _{LIN} in Ω, B is nonlinearity relative to V _{FS}			Ω
K _{LIN}	K _{LIN} linearization factor	V _{REF} = 5V		6.645			kΩ
		V _{REF} = 2.5V		9.905			kΩ
	Accuracy			±1	±5		%
	vs Temperature	T _A = -40°C to +85°C		±50	±100		ppm/°C
B	Maximum correctable sensor nonlinearity	V _{REF} = 5V		±5			% of V _{FS}
		V _{REF} = 2.5V		-2.5, +5			% of V _{FS}

- (1) Describes accuracy of the 4mA low-scale offset current. Does not include input amplifier effects. Can be trimmed to zero.
- (2) Does not include initial error or TCR of gain-setting resistor, R_G .
- (3) Increasing the full-scale input range improves nonlinearity.
- (4) Does not include zero output initial error.
- (5) Voltage measured with respect to I_{RET} pin.
- (6) Calculated using the box method: $(\text{MAX}_{(-40^\circ\text{C to } 85^\circ\text{C})} - \text{MIN}_{(-40^\circ\text{C to } 85^\circ\text{C})}) / \text{MIN}_{(-40^\circ\text{C to } 85^\circ\text{C})} / (85^\circ\text{C} - (-40^\circ\text{C}))$.
- (7) See also [セクション 6.3.1](#). V_{FS} = full-scale V_{IN} .

5.5 Typical Characteristics

at $T_A = +25^\circ\text{C}$, $V_+ = 24\text{V}$ (unless otherwise noted)

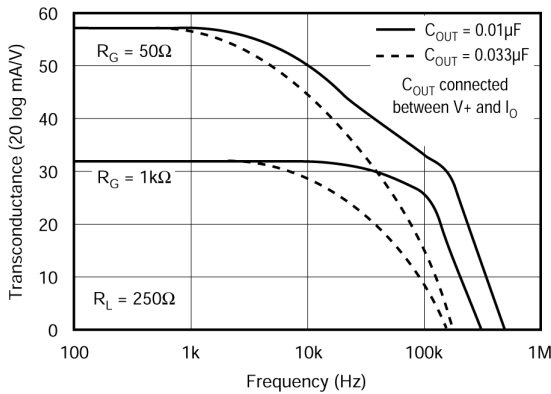


Figure 5-1. Transconductance vs Frequency

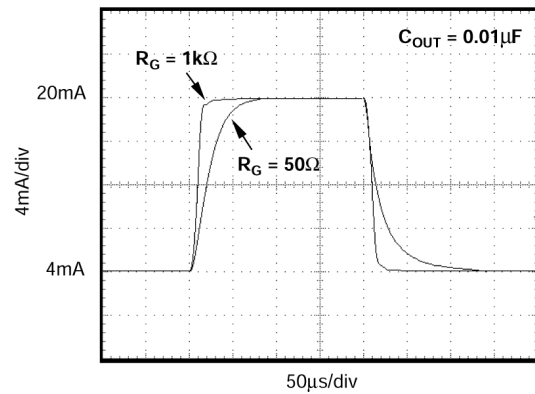


Figure 5-2. Step Response

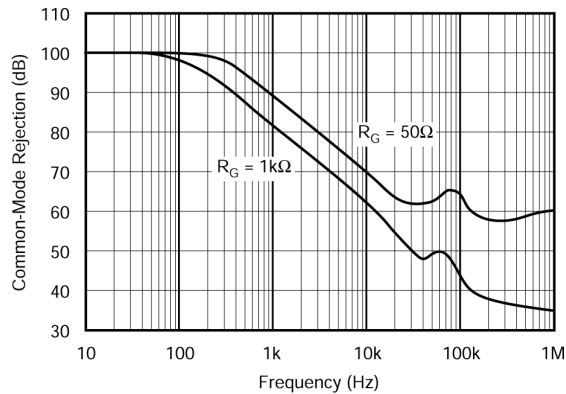


Figure 5-3. Common-Mode Rejection vs Frequency

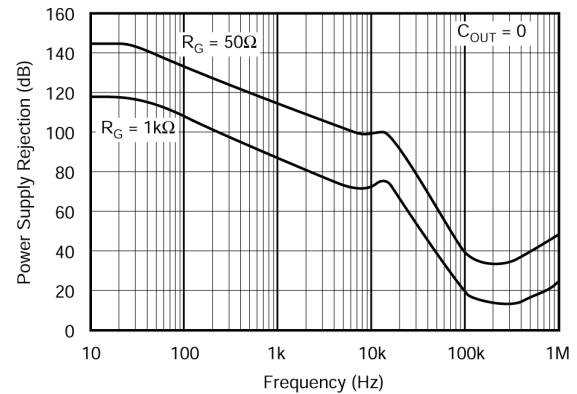


Figure 5-4. Power Supply Rejection vs Frequency

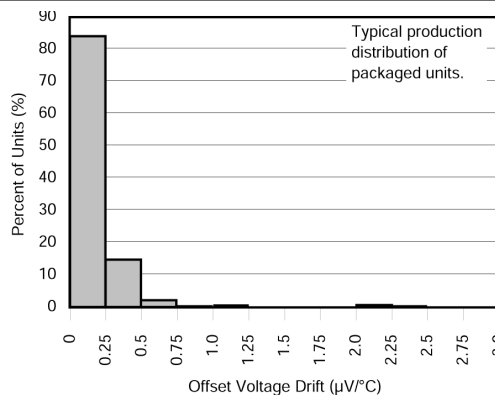


Figure 5-5. Input Offset Voltage Drift Production Distribution

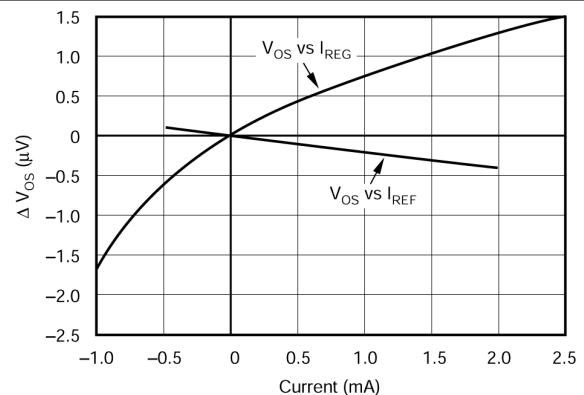


Figure 5-6. Input Offset Voltage Change vs V_{REG} And V_{REF} Currents

5.5 Typical Characteristics (continued)

at $T_A = +25^\circ\text{C}$, $V_+ = 24\text{V}$ (unless otherwise noted)

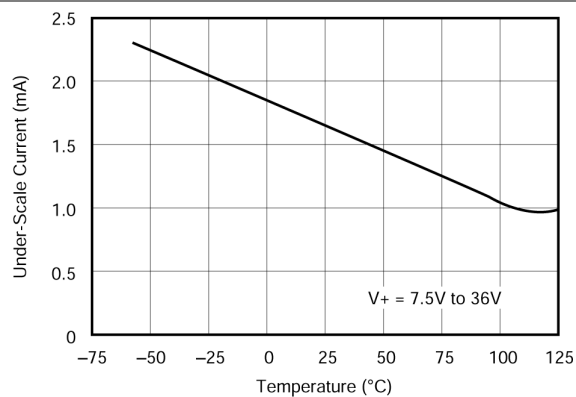


図 5-7. Underscale Current vs Temperature

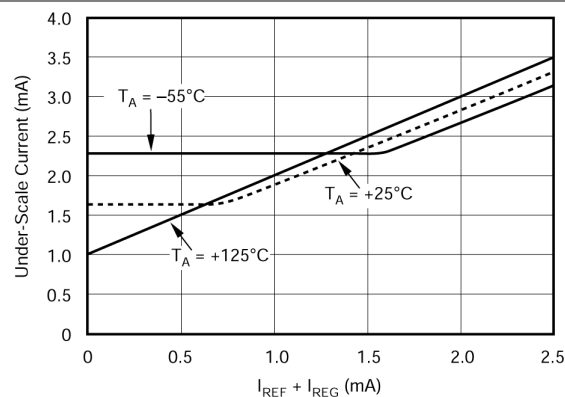


図 5-8. Underscale Current vs $I_{\text{REF}} + I_{\text{REG}}$

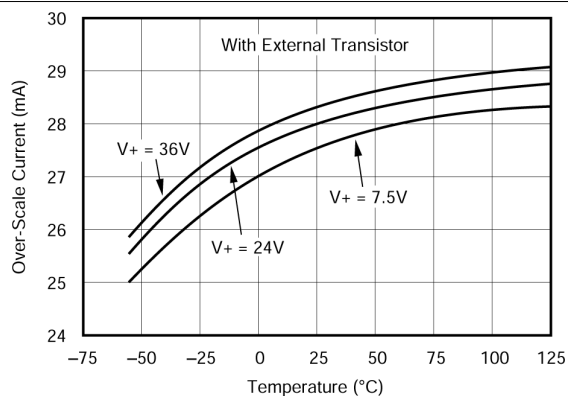


図 5-9. Overscale Current vs Temperature

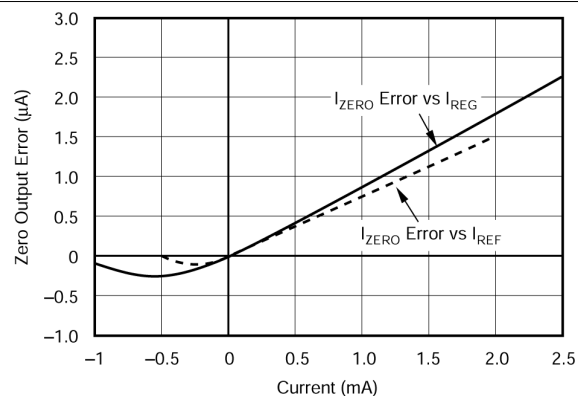


図 5-10. Zero Output Error vs V_{REF} and V_{REG} Currents

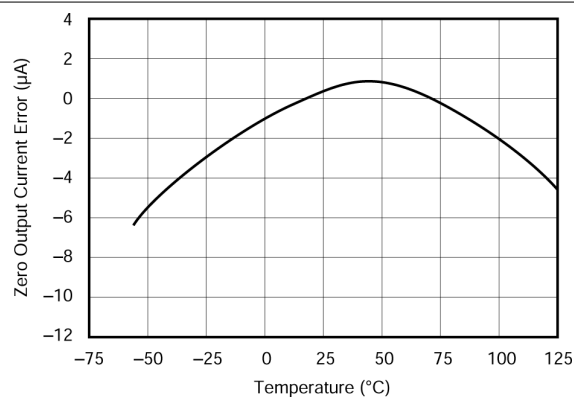


図 5-11. Zero Output Current Error vs Temperature

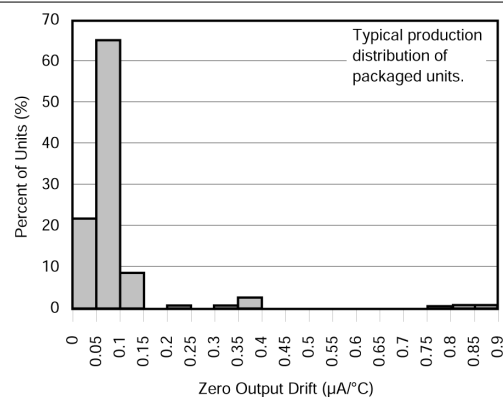


図 5-12. Zero Output Drift Production Distribution

5.5 Typical Characteristics (continued)

at $T_A = +25^\circ\text{C}$, $V_+ = 24\text{V}$ (unless otherwise noted)

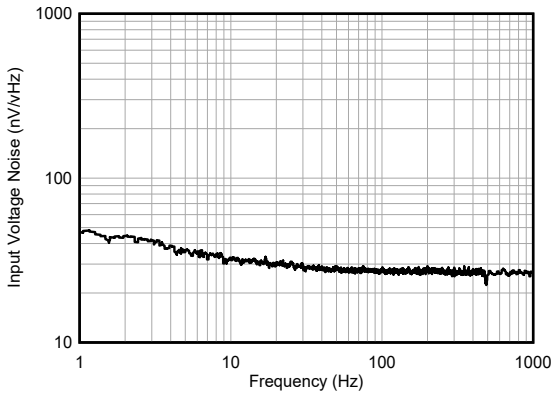


Figure 5-13. Input Voltage Noise Density vs Frequency

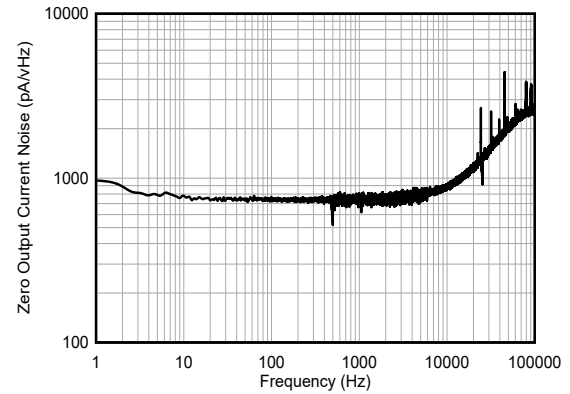


Figure 5-14. Zero Output Current Noise Density vs Frequency

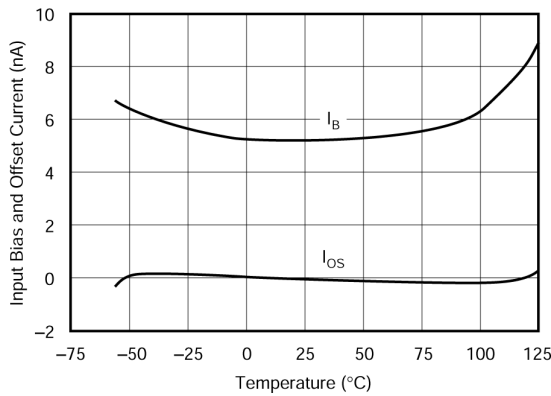


Figure 5-15. Input Bias and Offset Current vs Temperature

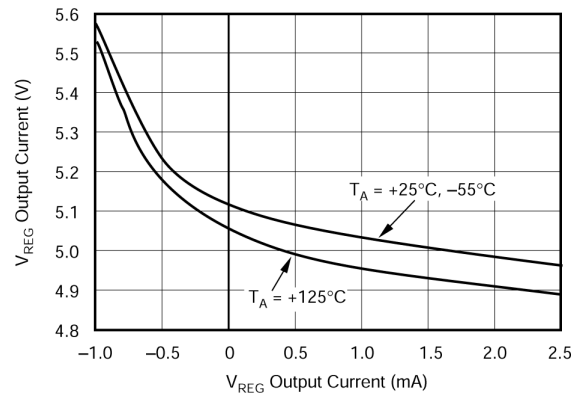


Figure 5-16. V_{REG} Output Voltage vs V_{REG} Output Current

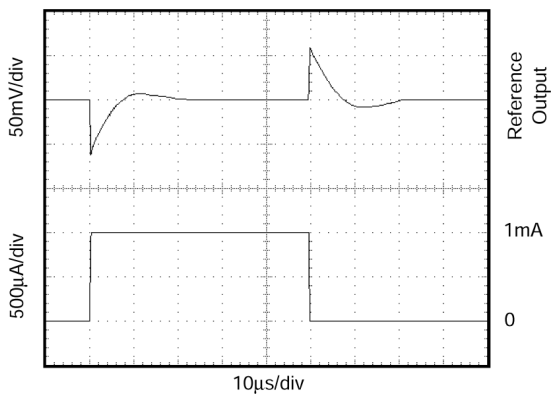


Figure 5-17. V_{REF5} Reference Transient Response

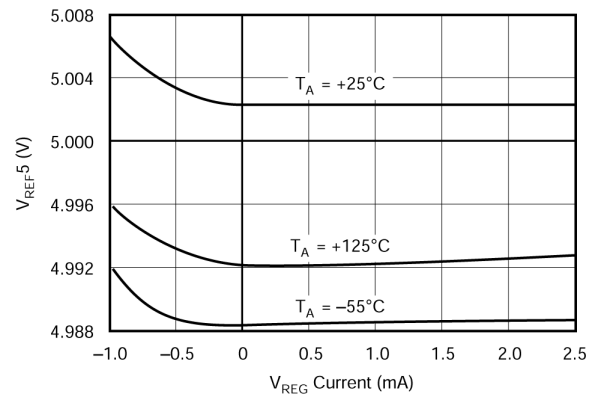


Figure 5-18. V_{REF5} vs V_{REG} Output Current

5.5 Typical Characteristics (continued)

at $T_A = +25^\circ\text{C}$, $V_+ = 24\text{V}$ (unless otherwise noted)

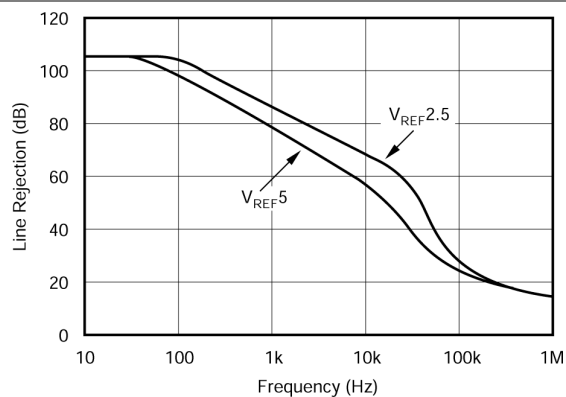


Figure 5-19. Reference AC Line Rejection vs Frequency

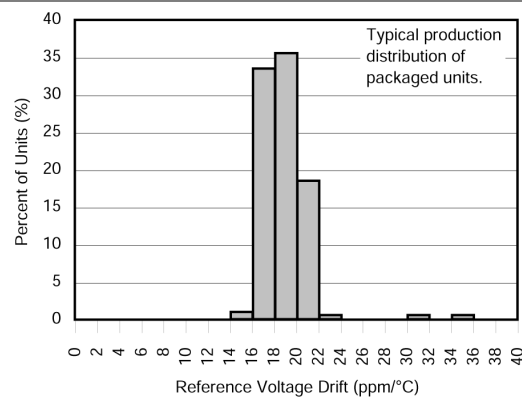


Figure 5-20. Reference Voltage Drift Production Distribution

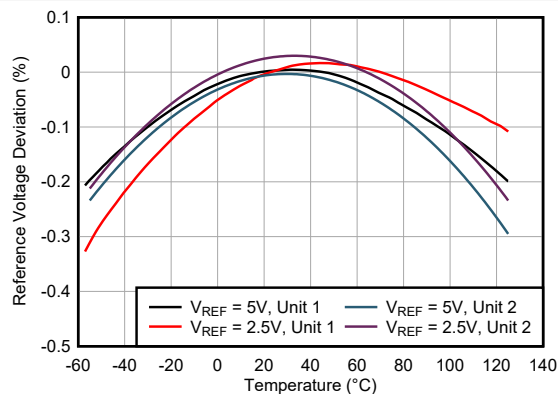


Figure 5-21. Reference Voltage Deviation vs Temperature

6 Detailed Description

6.1 Overview

The XTR106 is a monolithic 4mA-to-20mA, 2-wire current transmitter with a differential voltage input. 6-1 shows the simplified schematic of the XTR106. The loop power supply, V_+ , provides power for all circuitry. The output loop current is modulated by the XTR106 and is typically measured as a voltage across a series load resistor (R_L).

The instrumentation amplifier input of the XTR106 measures the voltage difference between the noninverting and inverting inputs. This difference is then gained up according to the value of R_G , and expressed as a regulated current output.

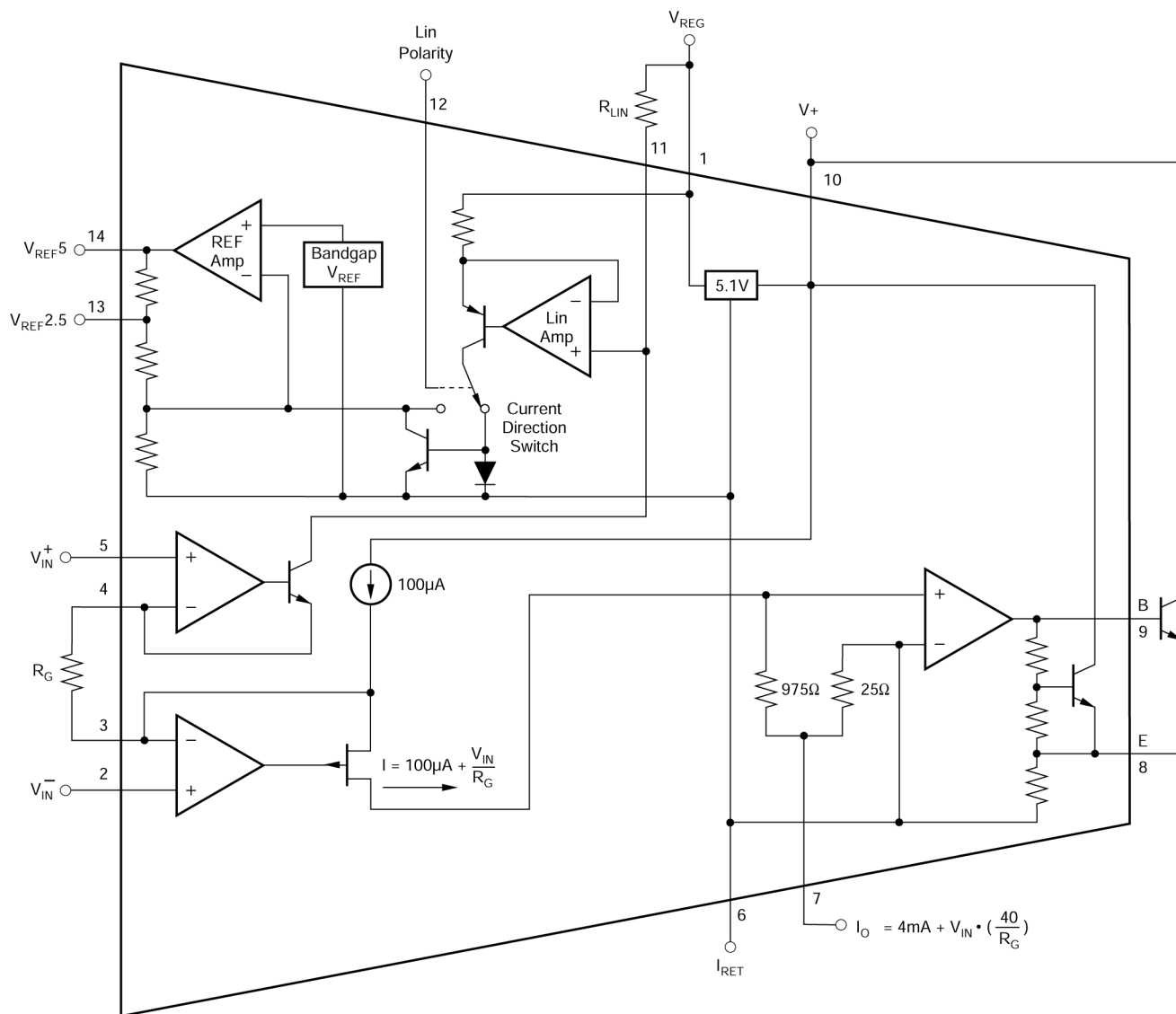
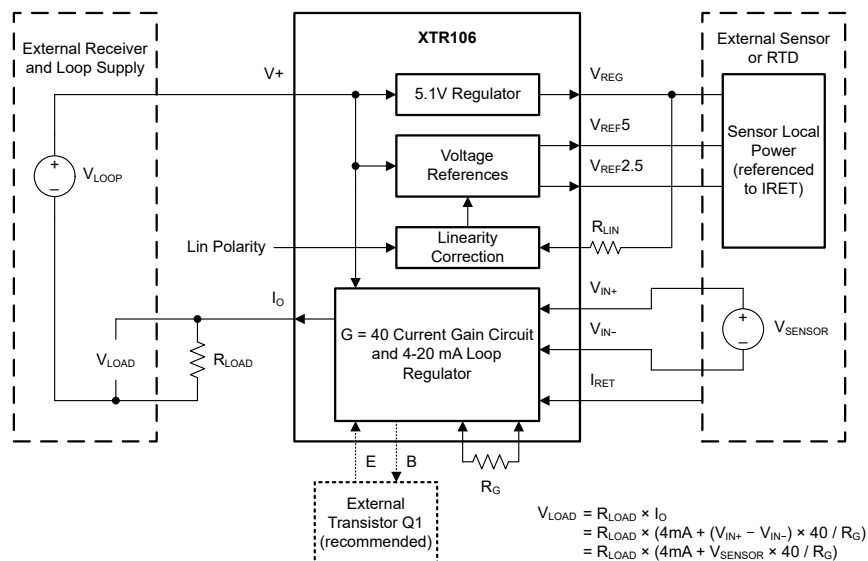


図 6-1. Simplified Schematic

6.2 Functional Block Diagram



6.3 Feature Description

6.3.1 Linearization

Many bridge sensors are inherently nonlinear. With the addition of one external resistor, compensating for parabolic nonlinearity with up to a 20:1 improvement over an uncompensated bridge output is possible.

Linearity correction is accomplished by varying the bridge excitation voltage. Signal-dependent variation of the bridge excitation voltage adds a second-order term to the overall transfer function (including the bridge). This configuration can be tailored to correct for bridge sensor nonlinearity.

Either positive or negative bridge nonlinearity errors can be compensated by proper connection of the Lin Polarity pin. To correct for positive bridge nonlinearity (upward bowing), connect Lin Polarity (pin 12) to I_{RET} (pin 6); see also [Figure 6-2](#). This correction causes V_{REF} to increase with bridge output, which compensates for a positive bow in the bridge response. To correct negative nonlinearity (downward bowing), connect Lin Polarity to V_{REG} (pin 1); see also [Figure 6-3](#). This correction causes V_{REF} to decrease with bridge output. The Lin Polarity pin is a high-impedance node.

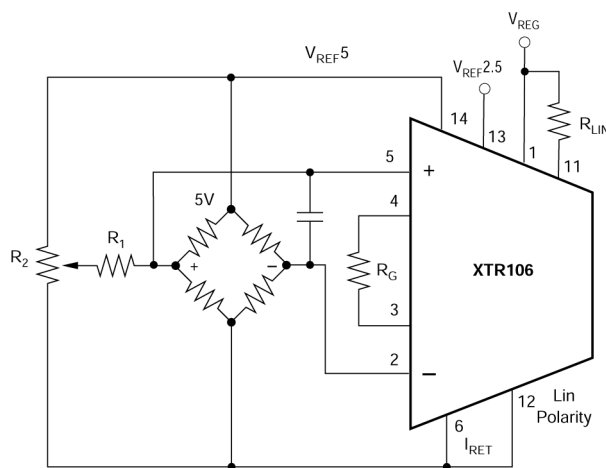


Figure 6-2. Connection for Positive Bridge Nonlinearity, V_{REF} = 5V

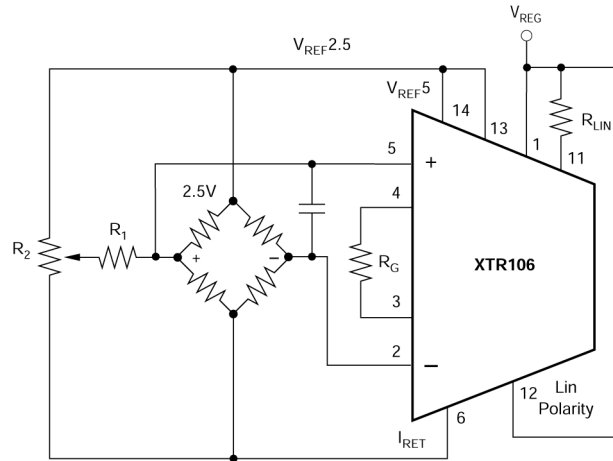


図 6-3. Connection for Negative Bridge Nonlinearity, $V_{REF} = 2.5V$

If no linearity correction is desired, connect both the R_{LIN} and Lin Polarity pins to V_{REG} (see also 図 6-4). This connection results in a constant reference voltage independent of input signal.

注

Do not leave the R_{LIN} or Lin Polarity pins open or connected to another potential.

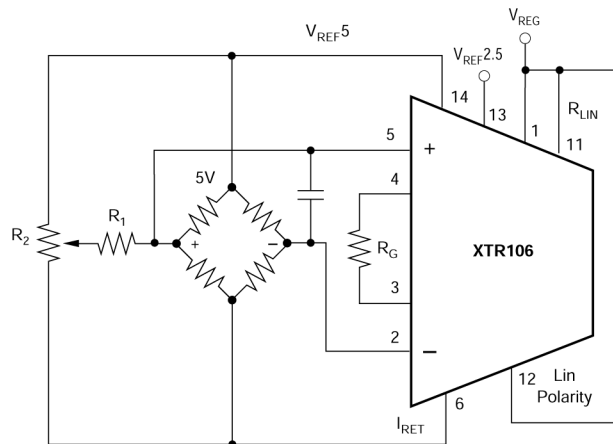


図 6-4. Connection if No Linearity Correction is Desired, $V_{REF} = 5V$

R_{LIN} is the external linearization resistor and is connected between pin 11 and pin 1 (V_{REG}); see also 図 6-2 and 図 6-3. To determine the value of R_{LIN} , the nonlinearity of the bridge sensor with constant excitation voltage must be known. The XTR106 linearity circuitry can only compensate for the parabolic-shaped portions of a sensor nonlinearity. Optimized correction occurs when maximum deviation from linear output occurs at midscale (see 図 7-3 and 図 7-4). Sensors with nonlinearity curves similar to that shown in 図 7-3 and 図 7-4, but not peaking exactly at midscale can be substantially improved.

A sensor with an S-shaped nonlinearity curve (equal positive and negative nonlinearity) cannot be improved with the XTR106 correction circuitry. The value of R_{LIN} is chosen according to 式 1. R_{LIN} depends on a linearization factor, K_{LIN} , which differs for the 2.5V reference and 5V reference. The sensor nonlinearity term, B (relative to full scale), is positive or negative depending on the direction of the bow.

Linearization resistor:

$$R_{LIN} = \left| K_{LIN} \times \frac{4B}{1-2B} \right| \quad (1)$$

where:

- K_{LIN} is the linearization factor (in Ω)
- K_{LIN} is 9905 Ω for the 2.5V reference
- K_{LIN} is 6645 Ω for the 5V reference
- B is the sensor nonlinearity relative to V_{FS} (for -2.5% nonlinearity, $B = -0.025$)
- V_{FS} is the full-scale bridge output without linearization (in V)

A maximum $\pm 5\%$ nonlinearity can be corrected when the 5V reference is used. Sensor nonlinearity of +5%/-2.5% can be corrected with 2.5V excitation. The trim circuit shown in 図 6-5 can be used for bridges with unknown bridge nonlinearity polarity.

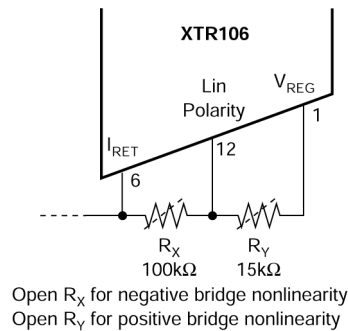


図 6-5. Onboard Resistor Circuit for Unknown Bridge Nonlinearity Polarity

Gain is affected by the varying excitation voltage used to correct bridge nonlinearity. The corrected value of the gain resistor is calculated from 式 2.

Gain-set resistor:

$$R_G = \frac{V_{FS}}{400\mu A} \times \frac{1+2B}{1-2B} \quad (2)$$

where:

- V_{FS} is the full-scale bridge output without linearization (in V)

When using linearity correction, keep the sensor output common-mode voltage within the XTR106 allowable input range of 1.1V to 3.5V. 式 3 can be used to calculate the XTR106 new excitation voltage. The common-mode voltage of the bridge output is simply half this value if no common-mode resistor is used (see also the examples in 図 6-2 and 図 6-3). Exceeding the common-mode range can yield unpredictable results.

Adjusted excitation voltage at full-scale output:

$$V_{REF} (Adj) = V_{REF} (Initial) \times \frac{1+2B}{1-2B} \quad (3)$$

For high-precision applications (errors < 1%), a two-step calibration process can be employed. First, the nonlinearity of the sensor bridge is measured with the initial gain resistor and $R_{LIN} = 0$ (R_{LIN} pin connected directly to V_{REF}). Using the resulting sensor nonlinearity, B , values for R_G and R_{LIN} are calculated using 式 1 and 式 2. A second calibration measurement is then taken to adjust R_G to account for the offsets and mismatches in the linearization.

Example:

Calculate R_{LIN} and the resulting R_G for a bridge sensor with 2.5% downward bow nonlinearity relative to V_{FS} and determine if the input common-mode range is valid.

For $V_{REF} = 2.5V$ and $V_{FS} = 50mV$

For a 2.5% downward bow, $B = -0.025$ (Lin Polarity pin connected to V_{REF})

For $V_{REF} = 2.5V$, $K_{LIN} = 9905\Omega$

$$R_{LIN} = \left| \frac{(9905\Omega)(4)(-0.025)}{1 - (2)(-0.025)} \right| = 943\Omega \quad (4)$$

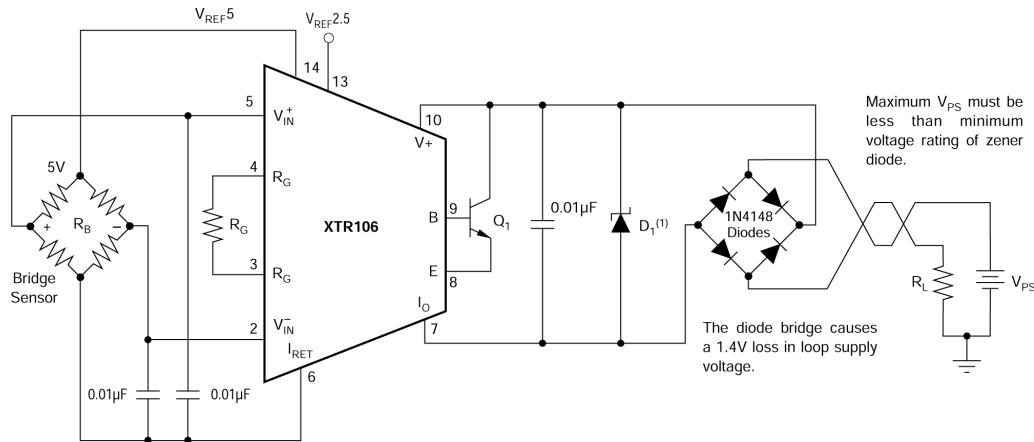
$$R_G = \frac{0.05V}{400\mu A} \times \frac{1 + (2)(-0.025)}{1 - (2)(-0.025)} = 113\Omega \quad (5)$$

$$V_{CM} = \frac{V_{REF} (Adj)}{2} = \frac{1}{2} \times 2.5V \times \frac{1 + (2)(-0.025)}{1 - (2)(-0.025)} = 1.13V \quad (6)$$

which falls within the 1.1V to 3.5V input common-mode range.

6.3.2 Reverse-Voltage Protection

The XTR106 low compliance rating (7.5V) permits the use of various voltage protection methods without compromising operating range. 図 6-6 shows a diode bridge circuit which allows normal operation even when the voltage connection lines are reversed. The bridge causes a two diode drop (approximately 1.4V) loss in loop-supply voltage. This results in a compliance voltage of approximately 9V—satisfactory for most applications. If a 1.4V drop in loop supply is too much, a diode can be inserted in series with the loop supply voltage and the $V+$ pin, as shown in 図 7-6. This protects against reverse output connection lines with only a 0.7V loss in loop-supply voltage.



(1) 36V Zener diode, such as 1N4753A or P6KE39A. Use lower-voltage Zener diodes with loop power-supply voltages < 30V for increased protection.

図 6-6. Reverse-Voltage Operation and Overvoltage Surge Protection

6.3.3 Overvoltage Surge Protection

Remote connections to current transmitters are sometimes subjected to voltage surges. Limit the maximum surge voltage applied to the XTR106 to the lowest practical value. Various Zener diode and surge clamping diodes are specially designed for this purpose. Select a clamp diode with as low a voltage rating as possible for best protection. For example, a 36V protection diode maintains proper transmitter operation at normal loop voltages, yet provides an appropriate level of protection against voltage surges. The XTR106 is specified to an absolute maximum loop voltage of 40V.

Most surge protection Zener diodes have a diode characteristic in the forward direction that conducts excessive current, possibly damaging receiving-side circuitry, if the loop connections are reversed. If a surge protection diode is used, use a series diode or diode bridge for protection against reversed connections.

6.4 Device Functional Modes

The device has one mode of operation that applies when operated within the *Recommended Operating Conditions*.

7 Application and Implementation

注

以下のアプリケーション情報は、TI の製品仕様に含まれるものではなく、TI ではその正確性または完全性を保証いたしません。個々の目的に対する製品の適合性については、お客様の責任で判断していただくことになります。お客様は自身の設計実装を検証しテストすることで、システムの機能を確認する必要があります。

7.1 Application Information

図 7-1 shows the basic connection diagram for the XTR106. The loop power supply, V_{PS} , provides power for all circuitry. Output loop current is measured as a voltage across the series load resistor, R_L . A 0.01 μ F to 0.03 μ F supply bypass capacitor connected between V_+ and I_O is recommended. For applications where fault, overload conditions, or both can saturate the inputs, a 0.03 μ F capacitor is recommended.

A 2.5V or 5V reference is available to excite a bridge sensor. For 5V excitation, connect pin 14 (V_{REF5}) to the bridge; see also 図 7-1. For 2.5V excitation, connect pin 13 ($V_{REF2.5}$) to pin 14; see also 図 6-3. The output terminals of the bridge are connected to the instrumentation amplifier inputs, V_{IN+} and V_{IN-} . A 0.01 μ F capacitor is shown connected between the inputs and is recommended for high impedance bridges ($> 10k\Omega$). The resistor R_G sets the gain of the instrumentation amplifier as required by the full-scale bridge voltage, V_{FS} .

Lin Polarity and R_{LIN} provide second-order linearization correction to the bridge, achieving up to a 20:1 improvement in linearity. Connections to Lin Polarity (pin 12) determine the polarity of nonlinearity correction; connect either to I_{RET} or V_{REG} . Connect Lin Polarity to V_{REG} even if linearity correction is not desired. R_{LIN} is chosen according to 式 7 and depends on K_{LIN} (linearization constant) and the bridge nonlinearity relative to V_{FS} (see セクション 6.3.1).

$$R_{LIN} = |K_{LIN} \times \frac{4B}{1-2B}| \quad (7)$$

where:

- K_{LIN} is in Ω

$$R_G = \left(\frac{V_{FS}}{400\mu A} \right) \times \frac{1+2B}{1-2B} \quad (8)$$

where:

- V_{FS} is in V
- $K_{LIN} = 9.905k\Omega$ for 2.5V reference
- $K_{LIN} = 6.645k\Omega$ for 5V reference
- B is the bridge nonlinearity relative to V_{FS}
- V_{FS} is the full-scale input voltage

The transfer function for the complete current transmitter is:

$$I_O = 4mA + V_{IN} \times \left(\frac{40}{R_G} \right) \quad (9)$$

Where:

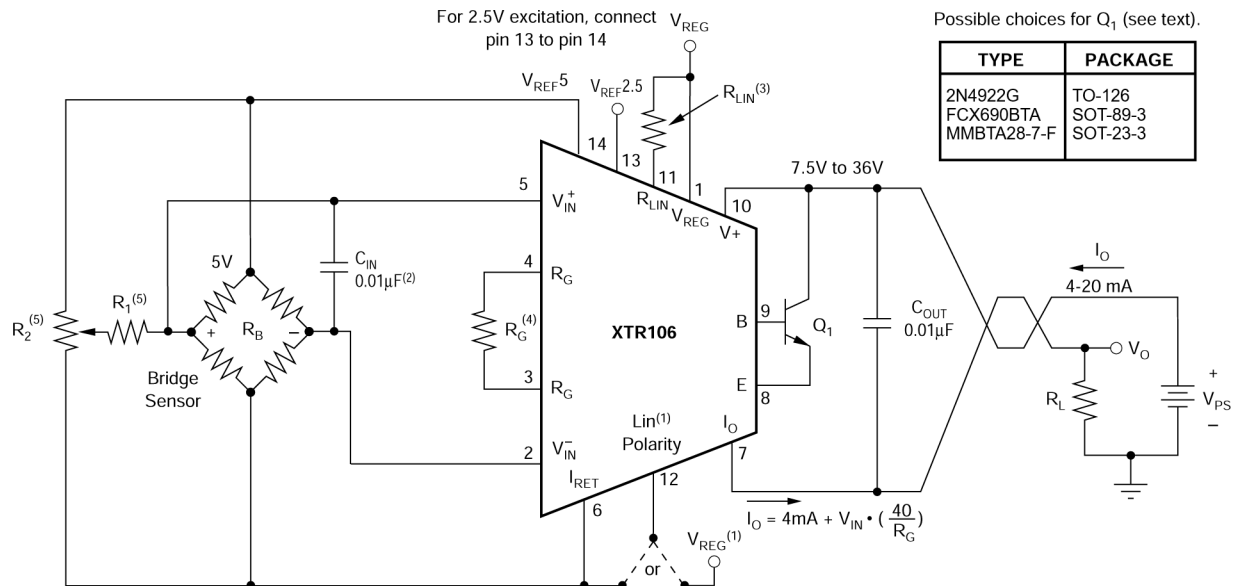
- V_{IN} is the differential input voltage in Volts
- R_G is in Ohms

As evident from the transfer function, if no R_G is used ($R_G = \infty$), the gain is zero and the output is simply the XTR106 zero current.

A negative input voltage, V_{IN} , causes the output current to be less than 4mA. Increasingly negative V_{IN} causes the output current to limit at approximately 1.6mA. If current is being sourced from the reference and/or V_{REG} , the current limit value can increase. See also [§ 5-7](#) and [§ 5-8](#).

Increasingly positive input voltage (greater than the full-scale input, V_{FS}) produces increasing output current according to the transfer function, up to the output current limit of approximately 28mA. See also [§ 5-9](#).

The I_{RET} pin is the return path for all current from the references and V_{REG} . I_{RET} also serves as a local ground and is the reference point for V_{REG} and the onboard voltage references. The I_{RET} pin allows any current used in external circuitry to be sensed by the XTR106 and to be included in the output current without causing error. The input voltage range of the XTR106 is referred to this pin.



(1) Connect Lin Polarity (pin 12) to I_{RET} (pin 6) to correct for positive bridge nonlinearity or connect to V_{REG} (pin 1) for negative bridge nonlinearity. The R_{LIN} pin and Lin Polarity pin must be connected to V_{REG} if linearity correction is not desired. Refer to the *Linearization* section.

(2) Recommended for bridge impedances > 10k Ω .

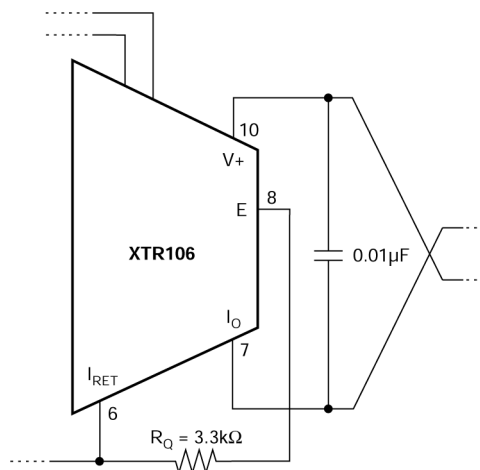
(3) R_1 and R_2 form bridge trim circuit to compensate for the initial accuracy of the bridge. See the *Bridge Balance* text.

7-1. Basic Bridge Measurement Circuit With Linearization

7.1.1 External Transistor

External pass transistor, Q_1 , conducts the majority of the signal-dependent 4mA-to-20mA loop current. Using an external transistor isolates the majority of the power dissipation from the precision input and reference circuitry of the XTR106, maintaining excellent accuracy.

The external transistor is inside a feedback loop; therefore, the characteristics are not critical. Requirements are: $V_{CEO} = 45V$ min, $\beta = 40$ min and $P_D = 800mW$. Power dissipation requirements can be lower if the loop power supply voltage is less than 36V. Some possible choices for Q_1 are listed in [Figure 7-1](#). The XTR106 can be operated without an external pass transistor. Accuracy, however, is somewhat degraded as a result of the internal power dissipation and subsequent self-heating. Operation without Q_1 is not recommended for extended temperature ranges. A resistor ($R = 3.3k\Omega$) connected between the I_{RET} pin and the E (emitter) pin is advised for operation less than 0°C without Q_1 to maintain the full 20mA full-scale output, especially with $V+$ near 7.5V.



(1) For operation without external transistor, connect a 3.3kΩ resistor between pin 6 and pin 8. See text for discussion of performance.

Figure 7-2. Operation Without an External Transistor

7.1.2 Loop Power Supply

The voltage applied to the XTR106, $V+$, is measured with respect to the I_O connection, pin 7. $V+$ can range from 7.5V to 36V. The loop-supply voltage, V_{PS} , differs from the voltage applied to the XTR106 according to the voltage drop on the current sensing resistor, R_L (plus any other voltage drop in the line).

If a low loop-supply voltage is used, R_L (including the loop wiring resistance) must be made a relatively low value so that $V+$ remains 7.5V or greater for the maximum loop current of 20mA:

$$R_{L\text{ MAX}} = \left(\frac{(V+) - 7.5V}{20mA} \right) - R_{\text{WIRING}} \quad (10)$$

For loop currents up to 30mA, design for $V+$ equal or greater than 7.5V to allow for out-of-range input conditions. $V+$ must be at least 8V if 5V sensor excitation is used and if correcting for bridge nonlinearity greater than +3%.

The low operating voltage (7.5V) of the XTR106 allows operation directly from personal computer power supplies (12V $\pm 5\%$). When used with the RCV420 Current Loop Receiver ([Figure 7-6](#)), load resistor voltage drop is limited to 3V.

7.1.3 Bridge Balance

Figure 7-1 shows a bridge trim circuit (R_1 , R_2). This adjustment can be used to compensate for the initial accuracy of the bridge, to trim the offset voltage of the XTR106, or both. The values of R_1 and R_2 depend on the impedance of the bridge, and the trim range required. This trim circuit places an additional load on the V_{REF} output. Be sure the additional load on V_{REF} does not affect zero output. See Figure 5-8. The effective load of the trim circuit is nearly equal to R_2 . An approximate value for R_1 can be calculated:

$$R_1 \approx \frac{5V \times R_B}{4 \times V_{TRIM}} \quad (11)$$

Where:

- R_B is the resistance of the bridge
- V_{TRIM} is the desired \pm voltage trim range (in V)

Make R_2 equal or lower in value to R_1 .

7.1.4 Underscale Current

The total current being drawn from the V_{REF} and V_{REG} voltage sources, as well as temperature, affect the XTR106 underscale current value (see Figure 5-8). Consider this when choosing the bridge resistance and excitation voltage, especially for transducers operating over a wide temperature range (see Figure 5-7).

7.1.5 Low-Impedance Bridges

The XTR106 two available excitation voltages (2.5V and 5V) allow the use of a wide variety of bridge values. Bridge impedances as low as $1k\Omega$ can be used without any additional circuitry. Lower impedance bridges can be used with the XTR106 by adding a series resistance to limit excitation current to $\leq 2.5mA$ (Figure 7-5). Add resistance to the upper and lower sides of the bridge to keep the bridge output within the 1.1V to 3.5V common-mode input range. Bridge output is reduced so a preamplifier can be needed to reduce offset voltage and drift.

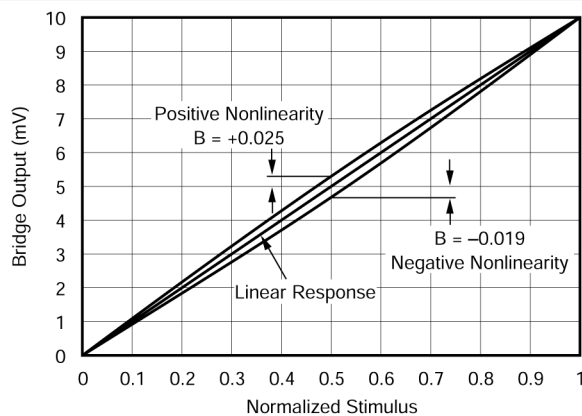


Figure 7-3. Bridge Transducer Transfer Function with Parabolic Nonlinearity

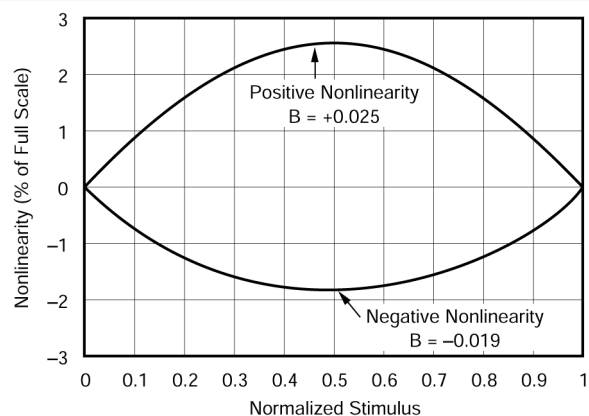
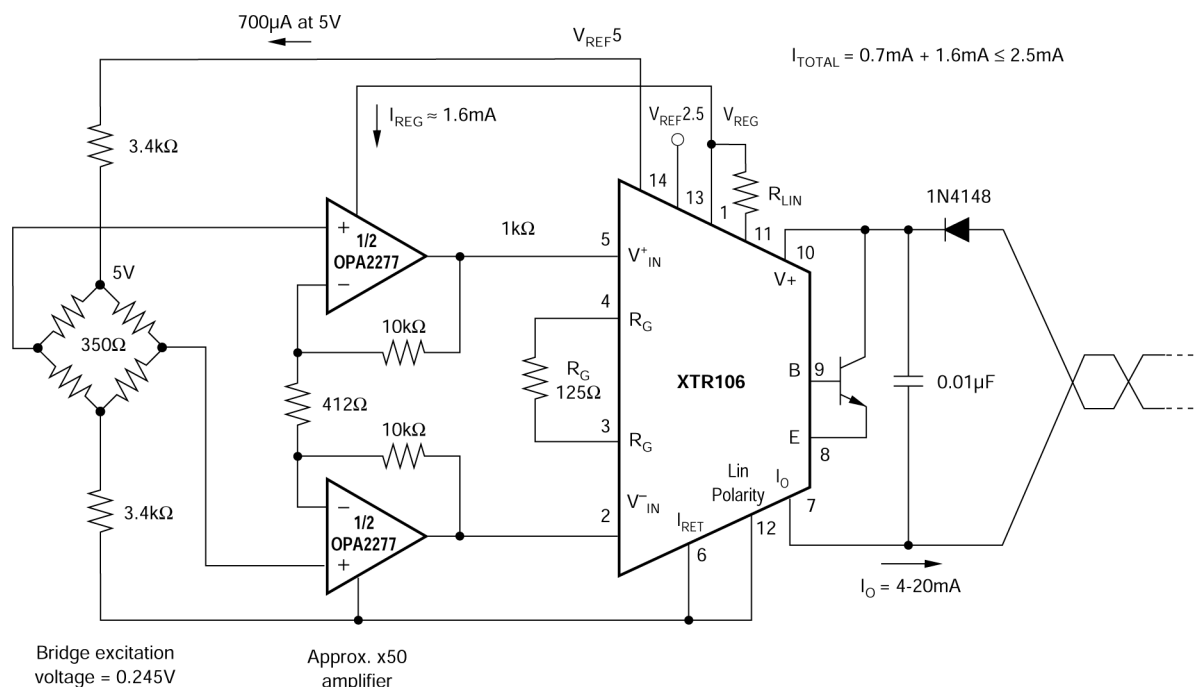


Figure 7-4. Nonlinearity vs Stimulus



(1) Shown connected to correct positive bridge nonlinearity. For negative bridge nonlinearity, see [Fig. 6-3](#).

7-5. 350Ω Bridge With x50 Preamplifier

7.1.6 Other Sensor Types

The XTR106 can be used with a wide variety of inputs. The high input impedance instrumentation amplifier is versatile and can be configured for differential input voltages from millivolts to a maximum of 2.4V full scale. The linear range of the inputs is from 1.1V to 3.5V, referenced to I_{RET}. The linearization feature of the XTR106 can be used with any sensor whose output is ratiometric with an excitation voltage.

7.1.7 Radio Frequency Interference

The long wire lengths of current loops invite radio frequency (RF) interference. RF interference can be rectified by the sensitive input circuitry of the XTR106 causing errors. These errors generally appears as an unstable output current that varies with the position of loop supply or input wiring.

If the bridge sensor is remotely located, the interference can enter at the input terminals. For integrated transmitter assemblies with short connection to the sensor, the interference more likely comes from the current loop connections.

Bypass capacitors on the input reduce or eliminate this input interference. 6-6 shows to connect these bypass capacitors to the I_{RET} pin. Although the dc voltage at the I_{RET} pin is not equal to 0V (at the loop supply, V_{PS}) this circuit point can be considered the transmitter ground. The 0.01 μ F capacitor connected between $V+$ and I_O can help minimize output interference.

7.1.8 Error Analysis

表 7-1 shows how to calculate the effect various error sources have on circuit accuracy. A sample error calculation for a typical bridge sensor measurement circuit (5kΩ bridge, $V_{REF} = 5V$, $V_{FS} = 50mV$) is provided. The results reveal the XTR106 excellent accuracy, in this case 1.2% unadjusted. Adjusting gain and offset errors improves circuit accuracy to 0.33%. These are worst-case errors; maximum values were used in the calculations and all errors were assumed to be positive (additive). The XTR106 achieves performance that is difficult to obtain with discrete circuitry and requires less board space.

表 7-1. Error Calculation

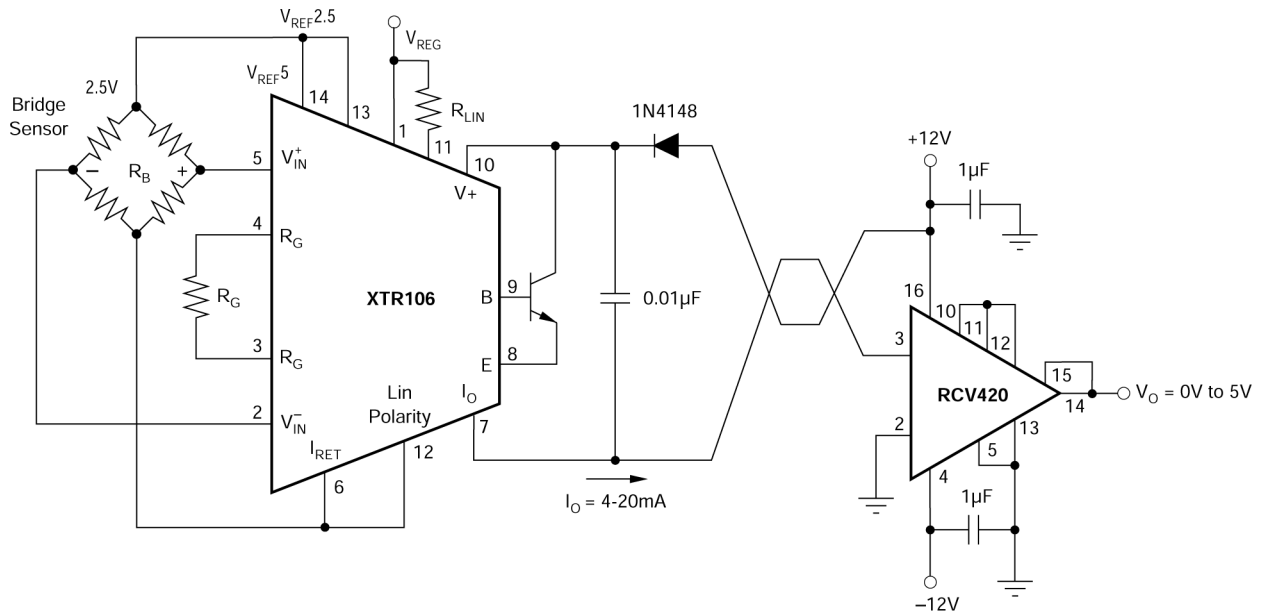
SAMPLE ERROR CALCULATION ⁽¹⁾				
Bridge Impedance (R _B) 5kΩ		Full Scale Input (V _{FS}) 50mV		
Ambient Temperature Range (ΔT _A) 20°C		Excitation Voltage (V _{REF}) 5V		
Supply Voltage Change (ΔV+) 5V		Common-Mode Voltage Change (ΔCM) 25mV (= V _{FS} /2)		
ERROR SOURCE	SAMPLE ERROR EQUATION	ERROR CALCULATION	ERROR (ppm of Full Scale)	
			UNADJ	ADJUST
INPUT				
Input offset voltage	V _{OS} /V _{FS} · 10 ⁶	200μV/50mV · 10 ⁶	2000	0
vs common-mode	CMRR · ΔCM/V _{FS} · 10 ⁶	50μV/V · 0.025V/50mV · 10 ⁶	25	25
vs power supply	(V _{OS} vs V+) · (ΔV+)/V _{FS} · 10 ⁶	3μV/V · 5V/50mV · 10 ⁶	300	300
Input bias current	CMRR · I _B · (R _B /2)/V _{FS} · 10 ⁶	50μV/V · 25nA · 2.5kΩ/50mV · 10 ⁶	0.1	0
Input offset current	I _{OS} · R _B /V _{FS} · 10 ⁶	3nA · 5kΩ/50mV · 10 ⁶	300	0
Total Input Error			2625	325
EXCITATION				
Voltage reference accuracy	V _{REF} Accuracy (%) / 100% · 10 ⁶	0.25% / 100% · 10 ⁶	2500	0
vs supply	(V _{REF} vs V+) · (ΔV+) · (V _{FS} /V _{REF})	20ppm/V · 5V (50mV/5V)	1	1
Total Excitation Error			2501	1
GAIN				
Span	Span Error (%) / 100% · 10 ⁶	0.2% / 100% · 10 ⁶	2000	0
Nonlinearity	Nonlinearity (%) / 100% · 10 ⁶	0.01% / 100% · 10 ⁶	100	100
Total Gain Error			2100	100
OUTPUT				
Zero output	I _{ZERO} – 4mA / 16000μA · 10 ⁶	25μA / 16000μA · 10 ⁶	1563	0
vs supply	(I _{ZERO} vs V+) · (ΔV+) / 16000μA · 10 ⁶	0.2μA/V · 5V / 16000μA · 10 ₆	62.5	62.5
Total Output Error			1626	63
DRIFT (ΔT _A = 20°C)				
Input offset voltage	Drift · ΔT _A / (V _{FS}) · 10 ⁶	1.5μV/°C · 20°C / (50mV) · 10 ⁶	600	600
Input offset current (typical)	Drift · ΔT _A · R _B / (V _{FS}) · 10 ⁶	5pA/°C · 20°C · 5kΩ / (50mV) · 10 ⁶	10	10
Voltage reference accuracy		35ppm/°C · 20°C	700	700
Span		225ppm/°C · 20°C	500	500
Zero output	Drift · ΔT _A / 16000μA · 10 ⁶	0.9μA/°C · 20°C / 16000μA · 10 ⁶	1125	1125
Total Drift Error			2936	2936
NOISE (0.1Hz to 10Hz, typical)				
Input offset voltage	V _n (p-p) / V _{FS} · 10 ⁶	0.6μV / 50mV · 10 ⁶	12	12
Zero output	I _{ZERO} Noise / 16000μA · 10 ⁶	0.035μA / 16000μA · 10 ⁶	2.2	2.2
Thermal R _B noise	[√2 · √(R _B /2) / 1kΩ · 4nV/√Hz · √10Hz] / V _{FS} · 10 ⁶	[√2 · √2.5kΩ / 1kΩ · 4nV/√Hz · √10Hz] / 50mV · 10 ⁶	0.6	0.6
Input current noise	(i _n · 40.8 · √2 · R _B /2) / V _{FS} · 10 ⁶	(200fA/√Hz · 40.8 · √2 · 2.5kΩ) / 50mV · 10 ⁶	0.6	0.6
Total Noise Error			15	15

表 7-1. Error Calculation (続き)

SAMPLE ERROR CALCULATION ⁽¹⁾				
Bridge Impedance (R _B) 5kΩ		Full Scale Input (V _{FS}) 50mV		
Ambient Temperature Range (ΔT _A) 20°C		Excitation Voltage (V _{REF}) 5V		
Supply Voltage Change (ΔV+) 5V		Common-Mode Voltage Change (ΔCM) 25mV (= V _{FS} /2)		
ERROR SOURCE	SAMPLE ERROR EQUATION	ERROR CALCULATION	ERROR (ppm of Full Scale)	
			UNADJ	ADJUST
			TOTAL ERROR:	
			11803	3340
			1.18%	0.33%

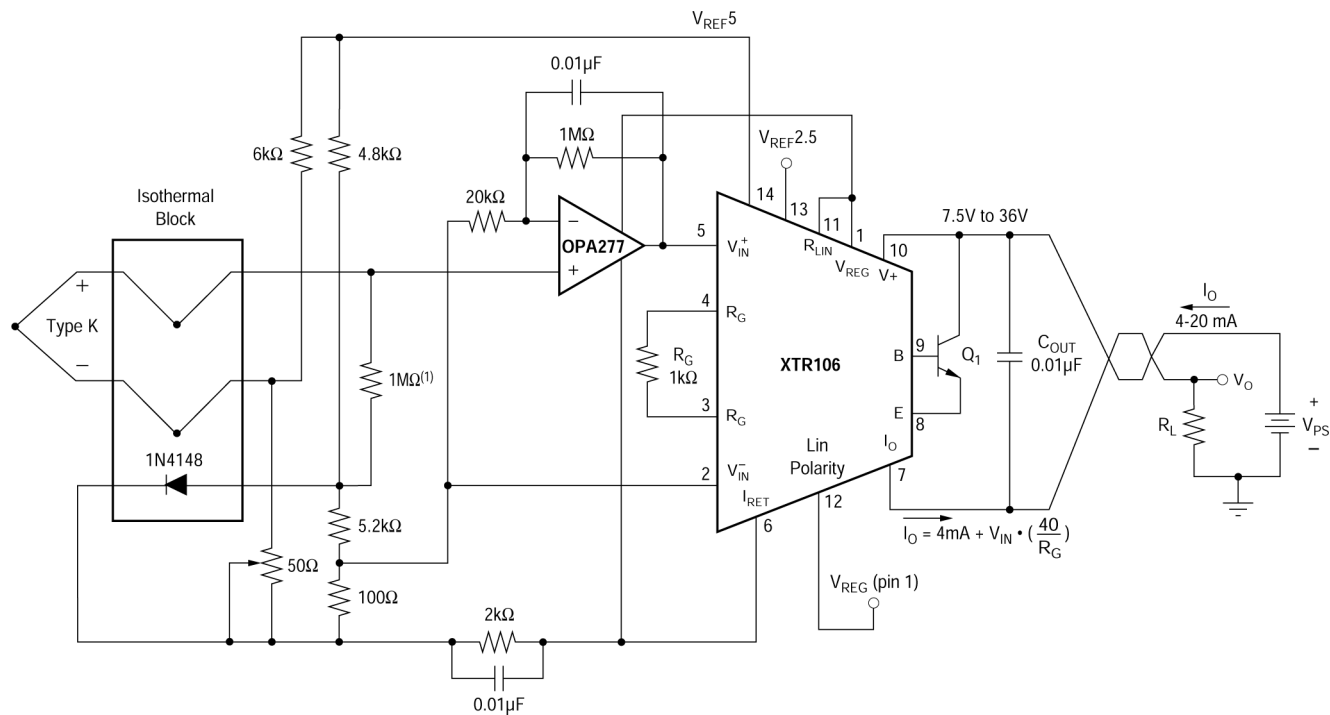
(1) All errors are minimum and maximum, and referred to input, unless otherwise stated.

7.2 Typical Applications



- (1) Lin Polarity shown connected to correct positive bridge nonlinearity. See 6-3 to correct negative bridge nonlinearity.
(2) See ISO124 data sheet if isolation is needed.

図 7-6. ±12V-Powered Transmitter and Receiver Loop



(1) For burn-out indication.

(2) See ISO124 data sheet if isolation is needed.

图 7-7. Thermocouple Low-Offset, Low-Drift Loop Measurement With Diode Cold-Junction Compensation

7.3 Layout

7.4 Layout Guidelines

The XTR106 is typically used with an external transistor (Q_1) to regulate the power dissipation of the 4mA to 20mA loop. This allows the resulting localized self-heating to be distanced from the precision circuitry of the XTR106 and reduces overtemperature drift errors.

The XTR106 can be used without the Q_1 transistor if the application requirements do not lead to violation of the device *Absolute Maximum Requirements*, such as the maximum junction temperature. Calculate the peak power dissipation and multiply by thermal resistance to approximate the associated junction temperature rise. Minimize overheat conditions for reliable long-term operation.

Place supply bypass capacitors close to the package and make connections with low-impedance conductors. Reduce trace lengths for R_G to minimize coupled environmental noise. If the loop power supply is electrically noisy, implement filtering using decoupling capacitors and small resistors or dampening inductors in series with V_+ .

8 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

8.1 Documentation Support

8.2 Related Documentation

For related documentation see the following:

- Texas Instruments, [Special Function Amplifiers Precision Labs video series](#) on Current Loop Transmitters
- Texas Instruments, [Analog Linearization of Resistance Temperature Detectors](#) technical article
- Texas Instruments, [A Basic Guide to RTD Measurements](#) application note

8.3 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、www.tij.co.jp のデバイス製品フォルダを開いてください。[通知] をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取ることができます。変更の詳細については、改訂されたドキュメントに含まれている改訂履歴をご覧ください。

8.4 サポート・リソース

テキサス・インスツルメンツ E2E™ サポート・フォーラムは、エンジニアが検証済みの回答と設計に関するヒントをエキスパートから迅速かつ直接得ることができる場所です。既存の回答を検索したり、独自の質問をしたりすることで、設計に必要な支援を迅速に得ることができます。

リンクされているコンテンツは、各寄稿者により「現状のまま」提供されるものです。これらはテキサス・インスツルメンツの仕様を構成するものではなく、必ずしもテキサス・インスツルメンツの見解を反映したものではありません。テキサス・インスツルメンツの[使用条件](#)を参照してください。

8.5 Trademarks

テキサス・インスツルメンツ E2E™ is a trademark of Texas Instruments.

すべての商標は、それぞれの所有者に帰属します。

8.6 静電気放電に関する注意事項



この IC は、ESD によって破損する可能性があります。テキサス・インスツルメンツは、IC を取り扱う際には常に適切な注意を払うことを推奨します。正しい取り扱いおよび設置手順に従わない場合、デバイスを破損するおそれがあります。

ESD による破損は、わずかな性能低下からデバイスの完全な故障まで多岐にわたります。精密な IC の場合、パラメータがわずかに変化するだけで公表されている仕様から外れる可能性があるため、破損が発生しやすくなっています。

8.7 用語集

[テキサス・インスツルメンツ用語集](#)

この用語集には、用語や略語の一覧および定義が記載されています。

9 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Changes from Revision A (November 2003) to Revision B (January 2025)	Page
• ドキュメント全体にわたって表、図、相互参照の採番方法を更新.....	1
• 「ピンの構成および機能」、「推奨動作条件」、「熱に関する情報」、「電気的特性」、「詳細説明」「機能ブロック図」、「アプリケーションと実装」、「代表的なアプリケーション」、「デバイスおよびドキュメントへのサポート」、「メカニカル、パッケージ、および注文情報」の各セクションを追加しました.....	1
• 「アプリケーション」セクションに最終機器を調整.....	1
• Moved operating and storage temperature parameters from <i>Electrical Characteristics</i> to <i>Absolute Maximum Ratings</i>	4
• Changed minimum operating temperature from -55°C to -40°C in <i>Absolute Maximum Ratings</i>	4

• Moved specified temperature and power-supply parameters from <i>Electrical Characteristics</i> to <i>Recommended Operating Conditions</i>	4
• Deleted thermal resistance, θ_{JA} parameters in <i>Electrical Characteristics</i> and replaced with detailed thermal model parameters in <i>Thermal Information</i>	4
• Added footnote regarding the use of the box method for the voltage references accuracy vs temperature specification in <i>Electrical Characteristics</i>	5
• Changed typical V_{REG} accuracy vs temperature specification from $\pm 0.3\text{mV}/^\circ\text{C}$ to $\pm 0.5\text{mV}/^\circ\text{C}$ in <i>Electrical Characteristics</i>	5
• Deleted <i>Input Voltage, Input Current, and Zero Output Current Noise Density vs Frequency</i> plot and replaced with Figure 5-13, <i>Input Voltage Noise Density vs Frequency</i> , and Figure 5-14, <i>Zero Output Current Noise Density vs Frequency</i>	7
• Updated Figure 5-20, <i>Reference Voltage Deviation vs Temperature</i>	7
• Changed description of maximum loop-supply voltage to specified absolute maximum rating in <i>Overvoltage Surge Protection</i>	16
• Updated suggested transistor part numbers in Figure 7-1, <i>Basic Bridge Measurement Circuit with Linearization</i>	17

10 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

重要なお知らせと免責事項

テキサス・インスツルメンツは、技術データと信頼性データ (データシートを含みます)、設計リソース (リファレンス デザインを含みます)、アプリケーションや設計に関する各種アドバイス、Web ツール、安全性情報、その他のリソースを、欠陥が存在する可能性のある「現状のまま」提供しており、商品性および特定目的に対する適合性の黙示保証、第三者の知的財産権の非侵害保証を含むいかなる保証も、明示的または黙示的にかかわらず拒否します。

これらのリソースは、テキサス・インスツルメンツ製品を使用する設計の経験を積んだ開発者への提供を意図したものです。(1) お客様のアプリケーションに適した テキサス・インスツルメンツ製品の選定、(2) お客様のアプリケーションの設計、検証、試験、(3) お客様のアプリケーションに該当する各種規格や、その他のあらゆる安全性、セキュリティ、規制、または他の要件への確実な適合に関する責任を、お客様のみが単独で負うものとします。

上記の各種リソースは、予告なく変更される可能性があります。これらのリソースは、リソースで説明されている テキサス・インスツルメンツ製品を使用するアプリケーションの開発の目的でのみ、テキサス・インスツルメンツはその使用をお客様に許諾します。これらのリソースに関して、他の目的で複製することや掲載することは禁止されています。テキサス・インスツルメンツや第三者の知的財産権のライセンスが付与されている訳ではありません。お客様は、これらのリソースを自身で使用した結果発生するあらゆる申し立て、損害、費用、損失、責任について、テキサス・インスツルメンツおよびその代理人を完全に補償するものとし、テキサス・インスツルメンツは一切の責任を拒否します。

テキサス・インスツルメンツの製品は、[テキサス・インスツルメンツの販売条件](#)、または [ti.com](https://www.ti.com) やかかる テキサス・インスツルメンツ製品の関連資料などのいずれかを通じて提供する適用可能な条項の下で提供されています。テキサス・インスツルメンツがこれらのリソースを提供することは、適用されるテキサス・インスツルメンツの保証または他の保証の放棄の拡大や変更を意味するものではありません。

お客様がいかなる追加条項または代替条項を提案した場合でも、テキサス・インスツルメンツはそれらに異議を唱え、拒否します。

郵送先住所: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265
Copyright © 2025, Texas Instruments Incorporated

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
XTR106P	Active	Production	PDIP (N) 14	25 TUBE	Yes	Call TI	N/A for Pkg Type	-40 to 85	XTR106P A
XTR106P.A	Active	Production	PDIP (N) 14	25 TUBE	Yes	Call TI	N/A for Pkg Type	-40 to 85	XTR106P A
XTR106PA	Active	Production	PDIP (N) 14	25 TUBE	Yes	Call TI	N/A for Pkg Type	-	XTR106P A
XTR106PA.A	Active	Production	PDIP (N) 14	25 TUBE	Yes	Call TI	N/A for Pkg Type	-40 to 85	XTR106P A
XTR106U/2K5	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	Call TI Nipdau	Level-3-260C-168 HR	-40 to 85	XTR106U
XTR106U/2K5.A	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	Call TI	Level-3-260C-168 HR	-40 to 85	XTR106U
XTR106U/2K5.B	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	Call TI	Level-3-260C-168 HR	-40 to 85	XTR106U
XTR106UA	Obsolete	Production	SOIC (D) 14	-	-	Call TI	Call TI	-40 to 85	XTR106U A
XTR106UA/2K5	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	Call TI Nipdau	Level-3-260C-168 HR	-40 to 85	(XTR106U, XTR106UA) A
XTR106UA/2K5.A	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	Call TI	Level-3-260C-168 HR	-40 to 85	(XTR106U, XTR106UA) A
XTR106UA/2K5.B	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	Call TI	Level-3-260C-168 HR	-40 to 85	(XTR106U, XTR106UA) A

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
XTR106U/2K5	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
XTR106UA/2K5	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
XTR106U/2K5	SOIC	D	14	2500	353.0	353.0	32.0
XTR106UA/2K5	SOIC	D	14	2500	353.0	353.0	32.0

TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (μm)	B (mm)
XTR106P	N	PDIP	14	25	506	13.97	11230	4.32
XTR106P.A	N	PDIP	14	25	506	13.97	11230	4.32
XTR106PA	N	PDIP	14	25	506	13.97	11230	4.32
XTR106PA.A	N	PDIP	14	25	506	13.97	11230	4.32

D0014A**PACKAGE OUTLINE****SOIC - 1.75 mm max height**

SMALL OUTLINE INTEGRATED CIRCUIT



4220718/A 09/2016

NOTES:

1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm, per side.
5. Reference JEDEC registration MS-012, variation AB.



**TEXAS
INSTRUMENTS**
www.ti.com

EXAMPLE BOARD LAYOUT

D0014A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



LAND PATTERN EXAMPLE
SCALE:8X



SOLDER MASK DETAILS

4220718/A 09/2016

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

D0014A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:8X

4220718/A 09/2016

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

N (R-PDIP-T**)

16 PINS SHOWN

PLASTIC DUAL-IN-LINE PACKAGE



PINS **	14	16	18	20
DIM				
A MAX	0.775 (19,69)	0.775 (19,69)	0.920 (23,37)	1.060 (26,92)
A MIN	0.745 (18,92)	0.745 (18,92)	0.850 (21,59)	0.940 (23,88)
MS-001 VARIATION	AA	BB	AC	AD



14/18 Pin Only
20 Pin vendor option

4040049/E 12/2002

- NOTES:
- A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 - Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
 - The 20 pin end lead shoulder width is a vendor option, either half or full width.

重要なお知らせと免責事項

TI は、技術データと信頼性データ (データシートを含みます)、設計リソース (リファレンス デザインを含みます)、アプリケーションや設計に関する各種アドバイス、Web ツール、安全性情報、その他のリソースを、欠陥が存在する可能性のある「現状のまま」提供しており、商品性および特定目的に対する適合性の黙示保証、第三者の知的財産権の非侵害保証を含むいかなる保証も、明示的または黙示的にかかわらず拒否します。

これらのリソースは、TI 製品を使用する設計の経験を積んだ開発者への提供を意図したものです。(1) お客様のアプリケーションに適した TI 製品の選定、(2) お客様のアプリケーションの設計、検証、試験、(3) お客様のアプリケーションに該当する各種規格や、その他のあらゆる安全性、セキュリティ、規制、または他の要件への確実な適合に関する責任を、お客様のみが単独で負うものとし、TI は一切の責任を拒否します。

上記の各種リソースは、予告なく変更される可能性があります。これらのリソースは、リソースで説明されている TI 製品を使用するアプリケーションの開発の目的でのみ、TI はその使用をお客様に許諾します。これらのリソースに関して、他の目的で複製することや掲載することは禁止されています。TI や第三者の知的財産権のライセンスが付与されている訳ではありません。お客様は、これらのリソースを自身で使用した結果発生するあらゆる申し立て、損害、費用、損失、責任について、TI およびその代理人を完全に補償するものとし、TI は一切の責任を拒否します。

TI の製品は、[TI の販売条件](#)、[TI の総合的な品質ガイドライン](#)、[ti.com](#) または TI 製品などに関連して提供される他の適用条件に従い提供されます。TI がこれらのリソースを提供することは、適用される TI の保証または他の保証の放棄の拡大や変更を意味するものではありません。TI がカスタム、またはカスタマー仕様として明示的に指定していない限り、TI の製品は標準的なカタログに掲載される汎用機器です。

お客様がいかなる追加条項または代替条項を提案する場合も、TI はそれらに異議を唱え、拒否します。

Copyright © 2025, Texas Instruments Incorporated

最終更新日：2025 年 10 月